

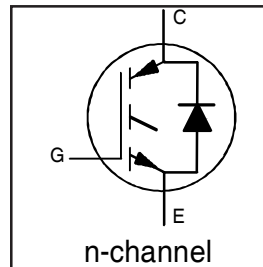
IRG4BC20UDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST
 SOFT RECOVERY DIODE

UltraFast CoPack IGBT

Features

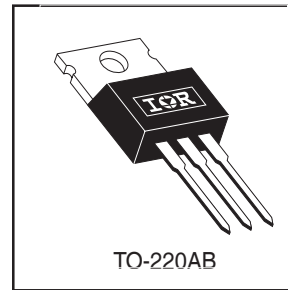
- UltraFast: optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED® ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.85V$
@ $V_{GE} = 15V, I_C = 6.5A$

Benefits

- Generation -4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs. Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	13	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.5	
I_{CM}	Pulsed Collector Current ①	52	
I_{LM}	Clamped Inductive Load Current ②	52	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
I_{FM}	Diode Maximum Forward Current	52	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_{STG}			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	2.1	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.50	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	80	
Wt	Weight	-----	2 (0.07)	-----	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	----	----	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	----	0.69	----	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	----	1.85	2.1	V	I _C = 6.5A V _{GE} = 15V
		----	2.27	----		I _C = 13A See Fig. 2, 5
		----	1.87	----		I _C = 6.5A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	----	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	----	-11	----	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	1.4	4.3	----	S	V _{CE} = 100V, I _C = 6.5A
I _{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	V _{GE} = 0V, V _{CE} = 600V
		----	----	1700		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	----	1.4	1.7	V	I _C = 8.0A See Fig. 13
		----	1.3	1.6		I _C = 8.0A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	----	27	41	nC	I _C = 6.5A
Q _{ge}	Gate - Emitter Charge (turn-on)	----	4.5	6.8		V _{CC} = 400V See Fig. 8
Q _{gc}	Gate - Collector Charge (turn-on)	----	10	16		V _{GE} = 15V
t _{d(on)}	Turn-On Delay Time	----	39	----	ns	T _J = 25°C
t _r	Rise Time	----	15	----		I _C = 6.5A, V _{CC} = 480V
t _{d(off)}	Turn-Off Delay Time	----	93	140		V _{GE} = 15V, R _G = 50Ω
t _f	Fall Time	----	110	170		Energy losses include "tail" and diode reverse recovery.
E _{on}	Turn-On Switching Loss	----	0.16	----	mJ	See Fig. 9, 10, 11, 18
E _{off}	Turn-Off Switching Loss	----	0.13	----		
E _{ts}	Total Switching Loss	----	0.29	0.3		
t _{d(on)}	Turn-On Delay Time	----	38	----	ns	T _J = 150°C, See Fig. 9, 10, 11, 18
t _r	Rise Time	----	17	----		I _C = 6.5A, V _{CC} = 480V
t _{d(off)}	Turn-Off Delay Time	----	100	----		V _{GE} = 15V, R _G = 50Ω
t _f	Fall Time	----	220	----		Energy losses include "tail" and diode reverse recovery.
E _{ts}	Total Switching Loss	----	0.49	----	mJ	
L _E	Internal Emitter Inductance	----	7.5	----	nH	Measured 5mm from package
C _{ies}	Input Capacitance	----	530	----	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	----	39	----		V _{CC} = 30V See Fig. 7
C _{res}	Reverse Transfer Capacitance	----	7.4	----		f = 1.0MHz
t _{rr}	Diode Reverse Recovery Time	----	37	55	ns	T _J = 25°C See Fig. 14
		----	55	90		T _J = 125°C
I _{rr}	Diode Peak Reverse Recovery Current	----	3.5	5.0	A	T _J = 25°C See Fig. 15
		----	4.5	8.0		T _J = 125°C
Q _{rr}	Diode Reverse Recovery Charge	----	65	138	nC	T _J = 25°C See Fig. 16
		----	124	360		T _J = 125°C
di _{(rec)M} /dt	Diode Peak Rate of Fall of Recovery During t _b	----	240	----	A/μs	T _J = 25°C See Fig. 17
		----	210	----		T _J = 125°C

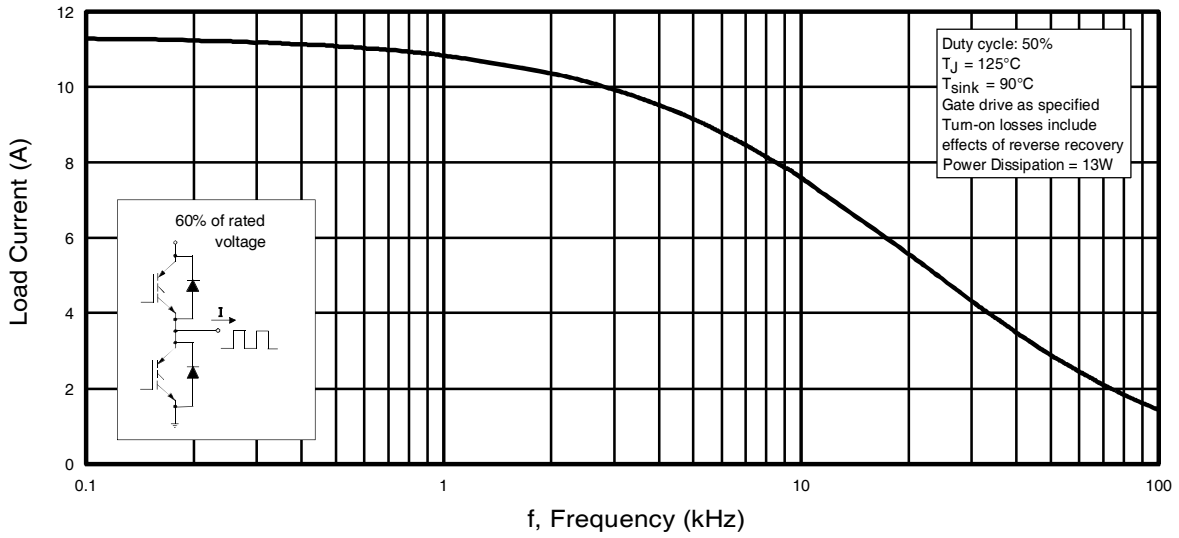


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

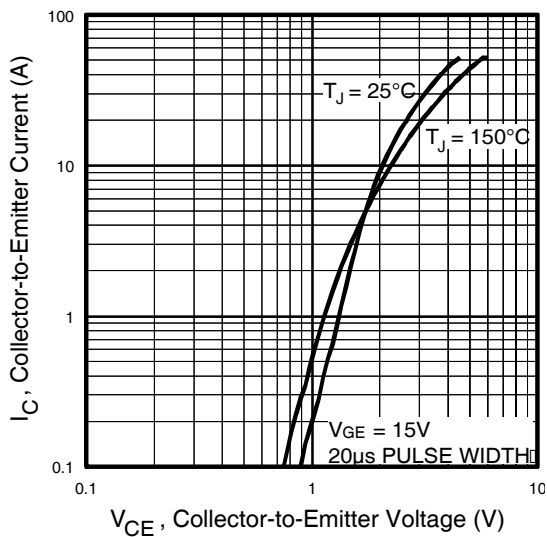


Fig. 2 - Typical Output Characteristics

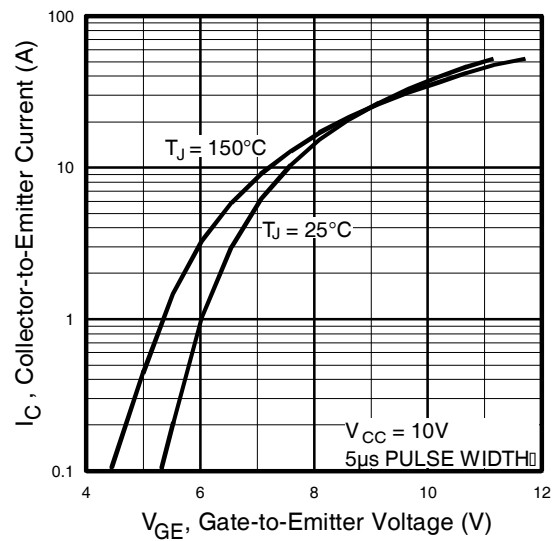


Fig. 3 - Typical Transfer Characteristics

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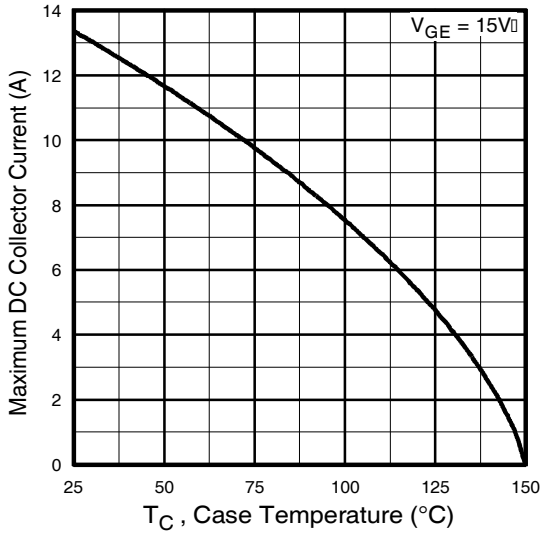


Fig. 4 - Maximum Collector Current vs. Case Temperature

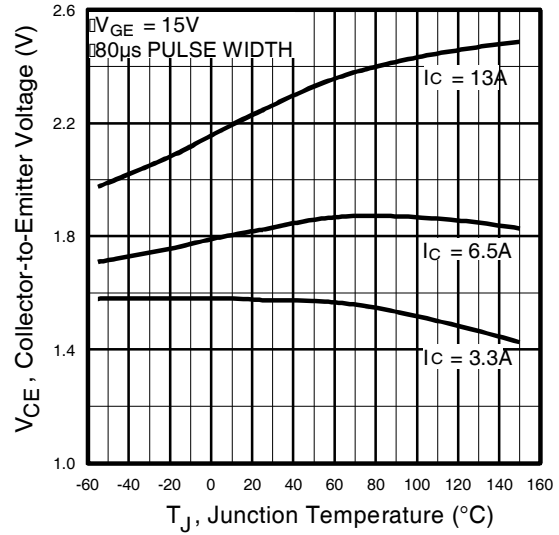


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

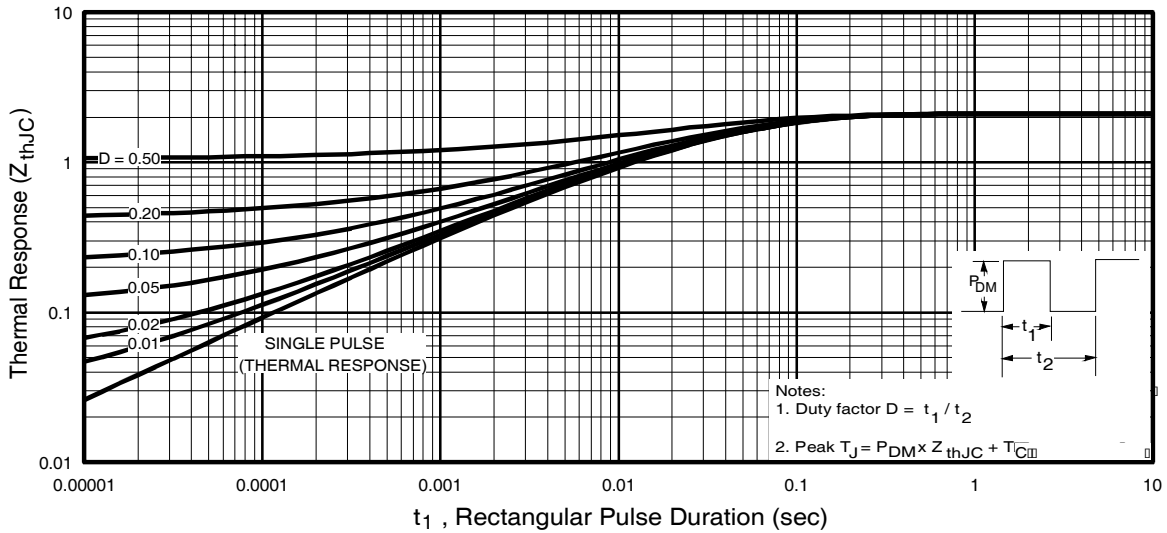


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

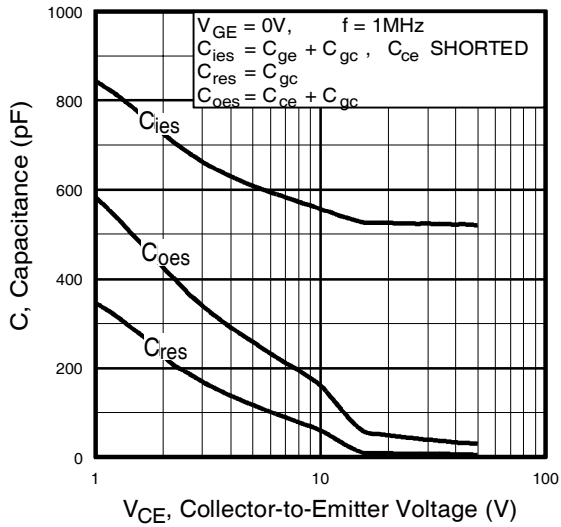


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

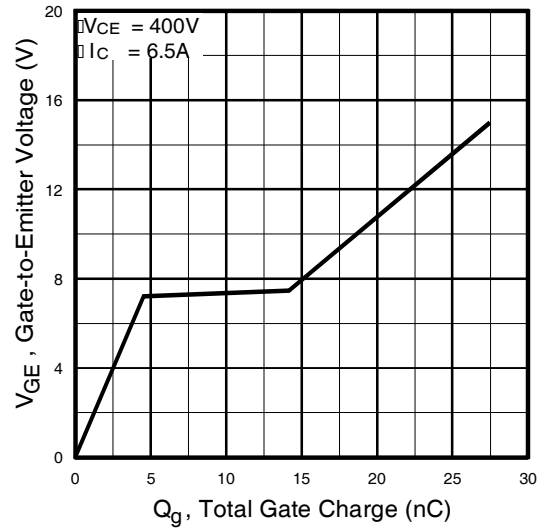


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

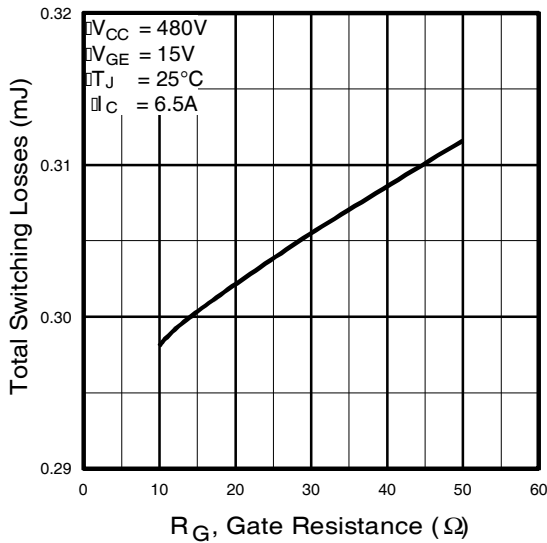


Fig. 9 - Typical Switching Losses vs. Gate Resistance

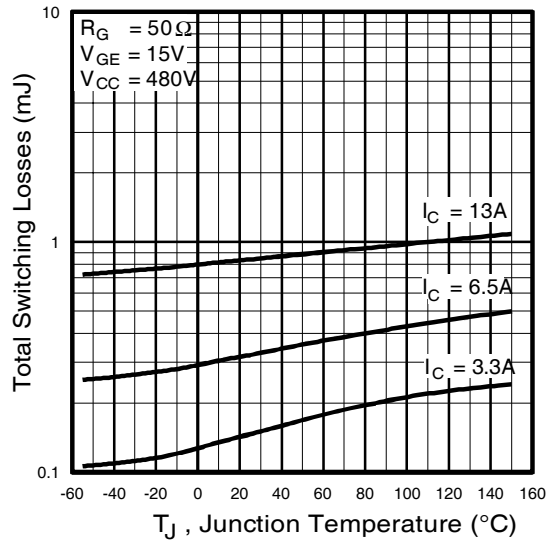


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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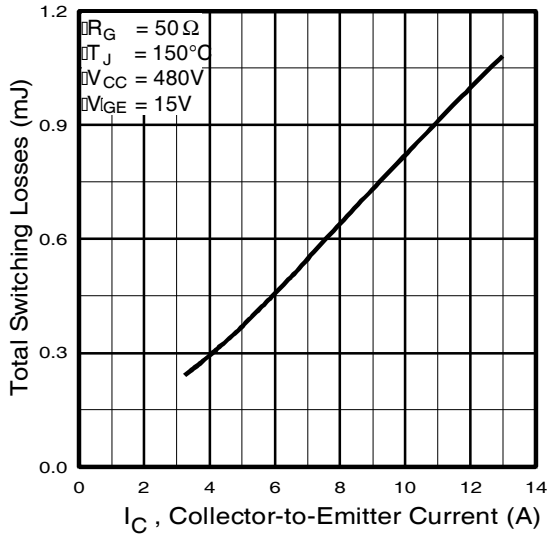


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

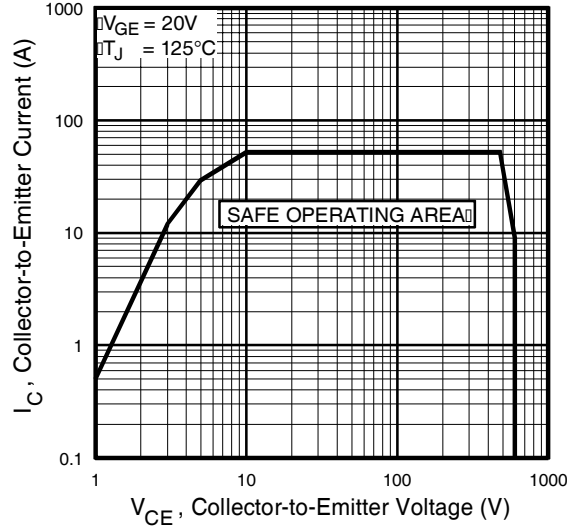


Fig. 12 - Turn-Off SOA

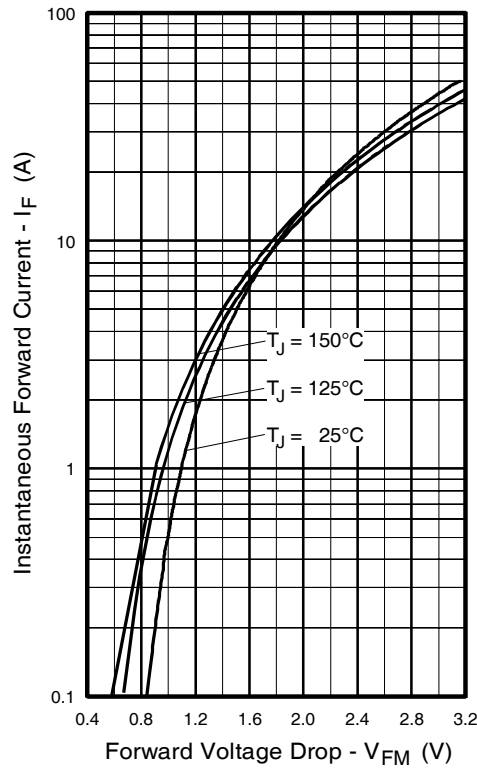


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

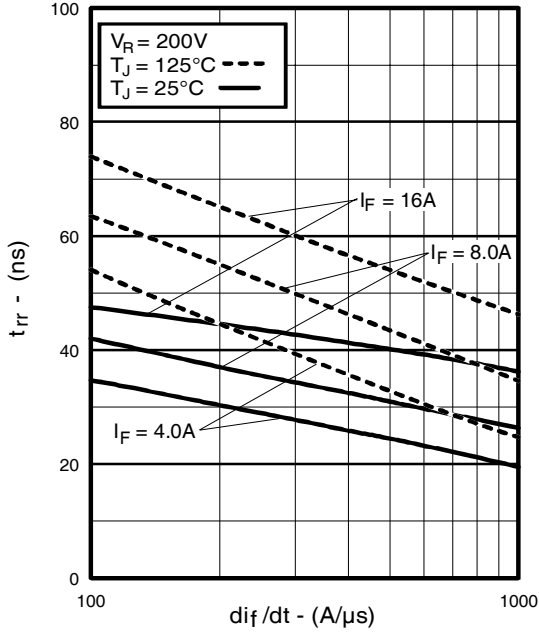


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

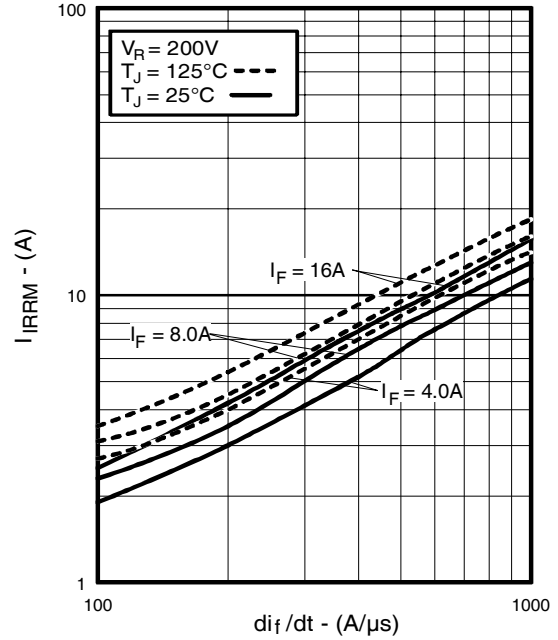


Fig. 15 - Typical Recovery Current vs. di_f/dt

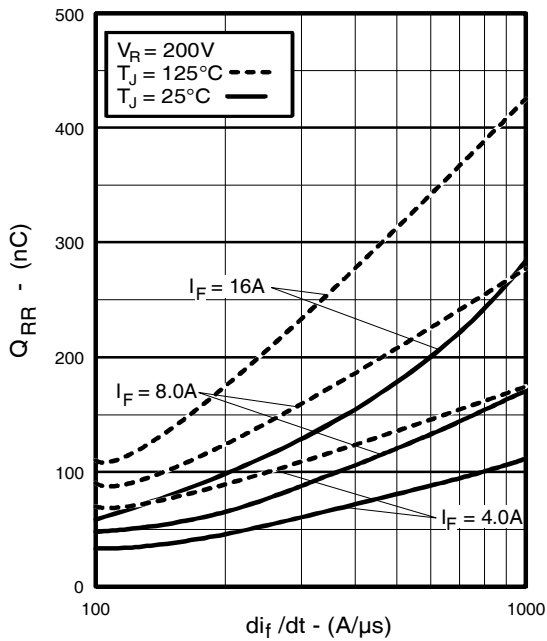


Fig. 16 - Typical Stored Charge vs. di_f/dt
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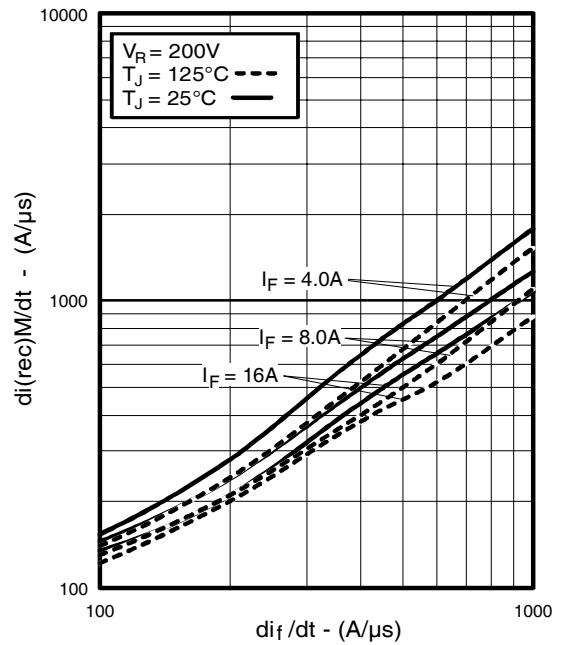


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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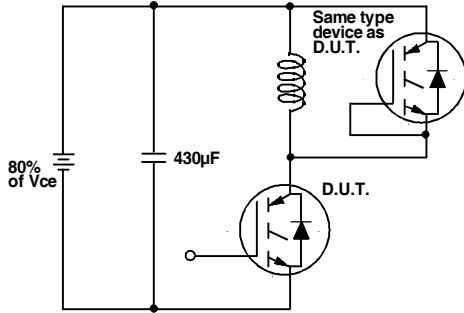


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

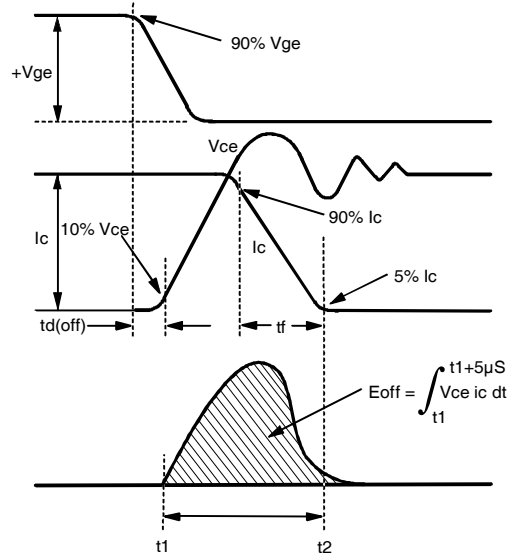


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

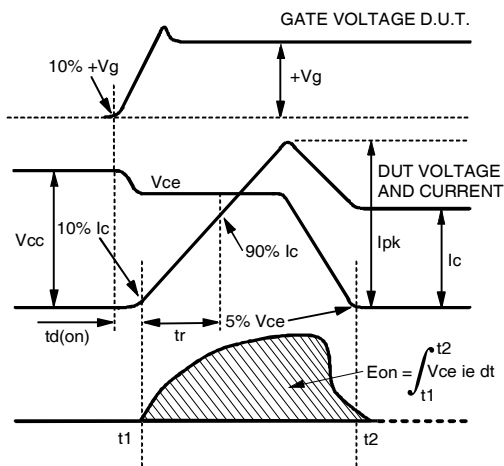


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

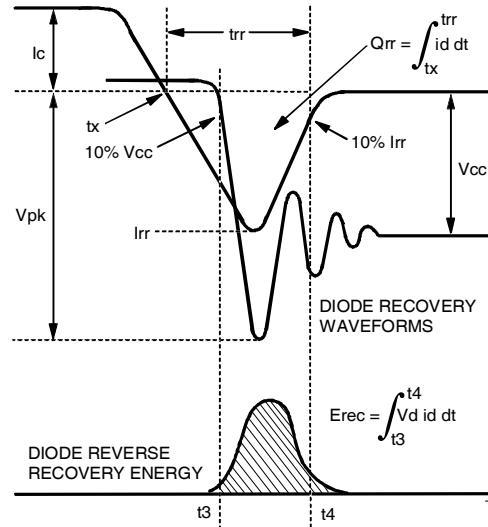


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

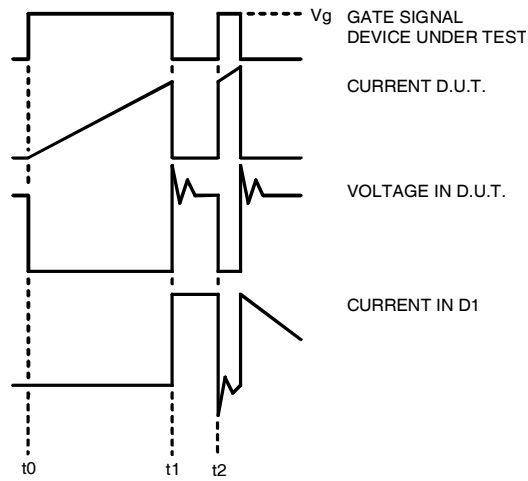


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

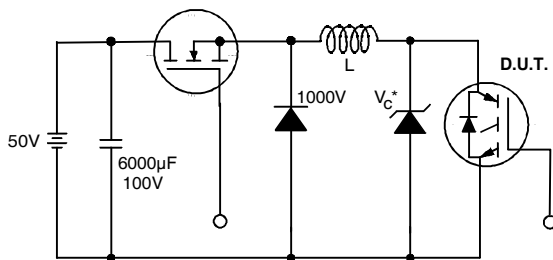


Figure 19. Clamped Inductive Load Test Circuit

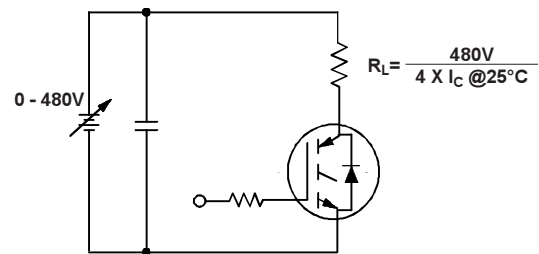


Figure 20. Pulsed Collector Current Test Circuit

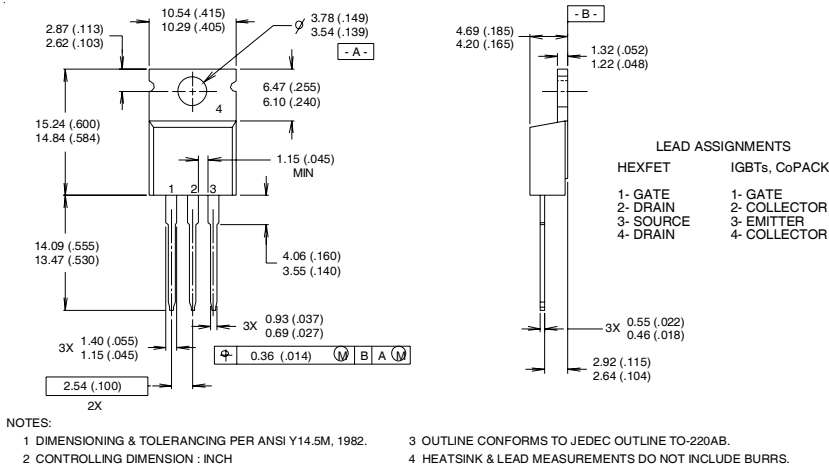
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Notes:

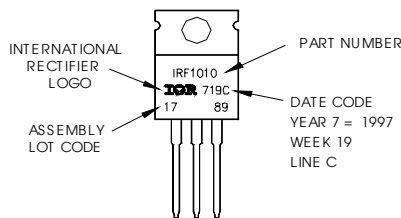
- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width 5.0 μs , single shot.

TO-220AB Package Outline



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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